






	<h2>SI3493DDV-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI3493DDV-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET P-CH 20V 8A 6TSOP</p> <p>Datenblätter:  SI3493DDV-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 6000 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI3493DDV-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 20V 8A 6TSOP
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	6000 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	SOT-23-6 Thin, TSOT-23-6
Supplier Device-Gehäuse	6-TSOP
Verlustleistung (max)	3.6W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	8A (Tc)
Rds On (Max) @ Id, Vgs	24 mOhm @ 7.5A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	30nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	1825pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)











SI3493DDV-T1-GE3 ist neu im Original, Suche SI3493DDV-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI3493DDV-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI3493DDV-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI3493DV-T1-E3 Vishay / Siliconix MOSFET P-CH 20V 5.3A 6-TSOP</p>	 <p>SI3493DV-T1 VISHAY SI3493DV-T1 VISHAY</p>	 <p>SI3493BDV-T1-E3-S VISHAY SI3493BDV-T1-E3-S VISHAY</p>	 <p>SI3493BDV-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 8A 6-TSOP</p>
 <p>SI3493DV-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 5.3A 6-TSOP</p>	 <p>SI3493DDV-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CHANNEL 20V 8A 6TSOP</p>	 <p>SI3493BDV-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 8A 6-TSOP</p>	 <p>SI3493DV VSHAY SI3493DV VSHAY</p>

heiße Teile

Mehr

 SI3475DV-T1-GE3	 SI3476DV-T1-E3	 SI3476DV-T1-GE3	 SI3476DV-T1-GE3	 SI3477DV-T1-E3
 SI3477DV-T1-GE3	 SI3477DV-T1-GE3	 SI3481DV-T1-E3	 SI3481DV-T1-E3	 SI3481DV-T1-GE3
 SI3481DV-T1-GE3	 SI3483CDV-T1-E3	 SI3483CDV-T1-E3	 SI3483CDV-T1-GE3	 SI3483CDV-T1-GE3
 SI3483DV-T1-E3	 SI3483DV-T1-E3	 SI3483DV-T1-GE3	 SI3483DV-T1-GE3	 SI3493BDV-T1-E3
 SI3493BDV-T1-E3	 SI3493BDV-T1-E3-S	 SI3493BDV-T1-GE3	 SI3493BDV-T1-GE3	 SI3493DDV-T1-GE3
 SI3493DV	 SI3493DV-T1	 SI3493DV-T1-E3	 SI3493DV-T1-E3	 SI3493DV-T1-E3
 SI3493DV-T1-GE3	 SI3493DV-T1-GE3	 SI3495DV	 SI3495DV-T1-E3	 SI3495DV-T1-E3
 SI3495DV-T1-GE3	 SI3495DV-T1-GE3	 SI3499DV-T1-E3	 SI3499DV-T1-E3	 SI3499DV-T1-GE3
 SI3499DV-T1-GE3	 SI3500-A-GM	 SI3529DV-T1-GE3	 SI3529DV-T1-GE3	 SI3552DV
 SI3552DV-T1	 SI3552DV-T1-E3	 SI3552DV-T1-E3	 SI3552DV-T1-GE3	 SI3552DV-T1-GE3

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